

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-20V	30mΩ @ V _{GS} = -4.5V	-6.0A
	39mΩ @ V _{GS} = -2.5V	-5.5A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

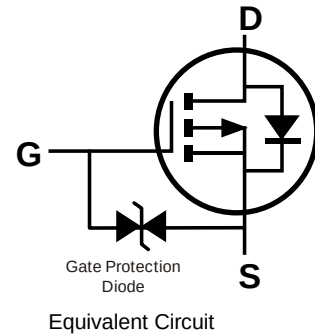
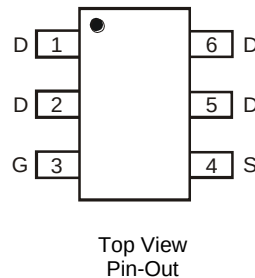
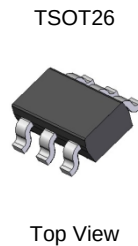
- DC-DC Converters
- Motor Control
- Power Management Functions
- Analog Switch

Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- ESD Protected
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe;
Solderable per MIL-STD-202, Method 208 **e3**
- Weight: 0.013 grams (Approximate)

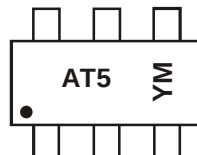


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2036UVT-7	TSOT26	3,000/Tape & Reel
DMP2036UVT-13	TSOT26	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



AT5 = Product Type Marking Code
 YM = Date Code Marking
 Y or Y̅ = Year (ex: F = 2018)
 M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-6.0 -5.0	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-40	A
Continuous Source-Drain Diode Current (Note 6)			I _S	-2.2	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	-21	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	23	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.1	W
	T _A = +70°C		0.7	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	108	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.5	W
	T _A = +70°C		1.0	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	81	°C/W
Thermal Resistance, Junction to Case (Note 6)	Steady State	R _{θJC}	16	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1	µA	V _{DS} = -16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	µA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	24	30	mΩ	V _{GS} = -4.5V, I _D = -6.4A
			31	39		V _{GS} = -2.5V, I _D = -4.8A
			41	58		V _{GS} = -1.8V, I _D = -2.5A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	1,808	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	155	—		
Reverse Transfer Capacitance	C _{rss}	—	117	—		
Gate Resistance	R _g	—	32	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	20.5	—	nC	V _{DS} = -10V, V _{GS} = -4.5V, I _D = -4.0A
Gate-Source Charge	Q _{gs}	—	2.8	—		
Gate-Drain Charge	Q _{gd}	—	4.1	—		
Turn-On Delay Time	t _{D(ON)}	—	9.1	—	ns	V _{DS} = -10V, V _{GS} = -4.5V, R _g = 6Ω, I _D = -1.0A
Turn-On Rise Time	t _r	—	12.3	—		
Turn-Off Delay Time	t _{D(OFF)}	—	120	—		
Turn-Off Fall Time	t _f	—	54	—		
Reverse Recovery Time	t _{RR}	—	23.1	—	ns	I _F = -1.0A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	8.3	—	nC	I _F = -1.0A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

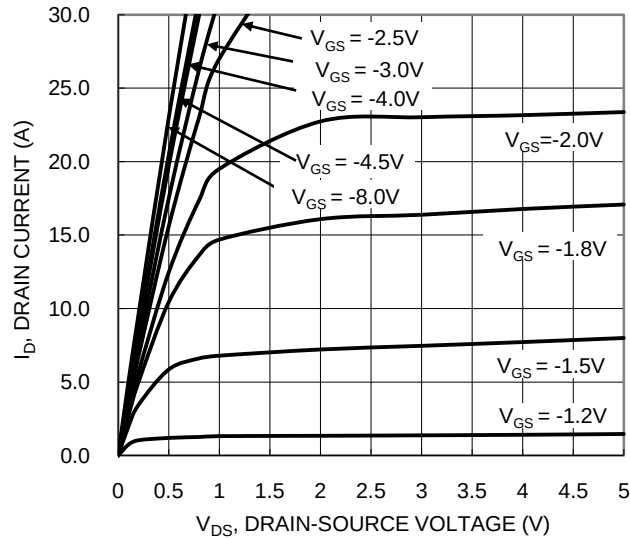


Figure 1. Typical Output Characteristic

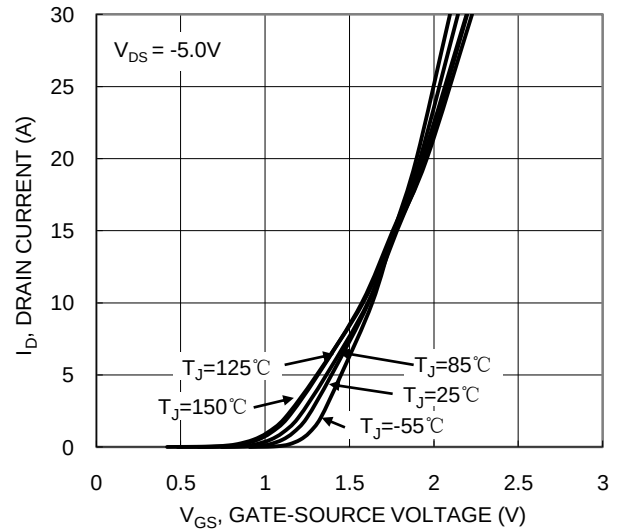


Figure 2. Typical Transfer Characteristic

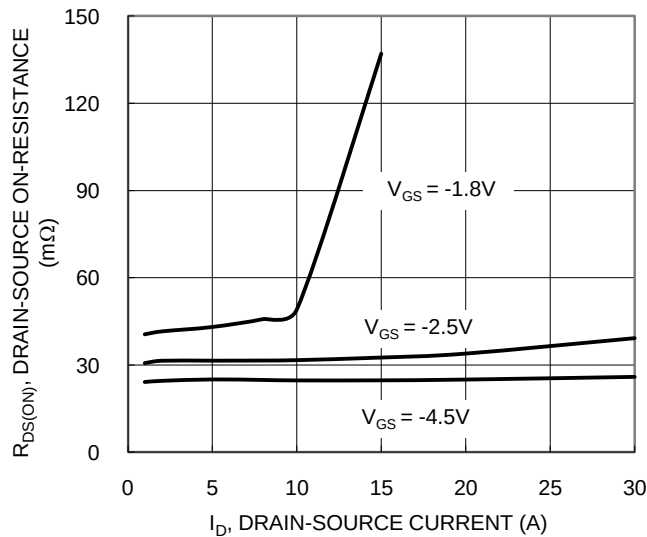


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

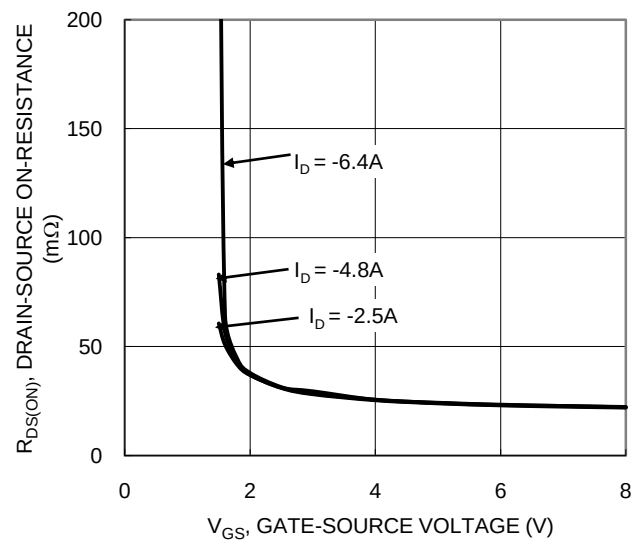


Figure 4. Typical Transfer Characteristic

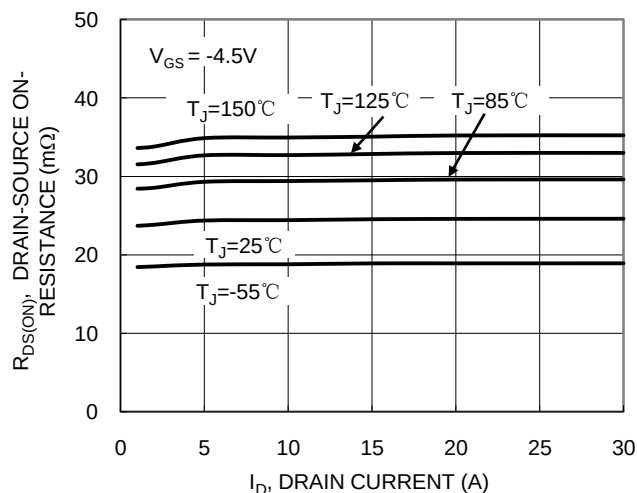


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

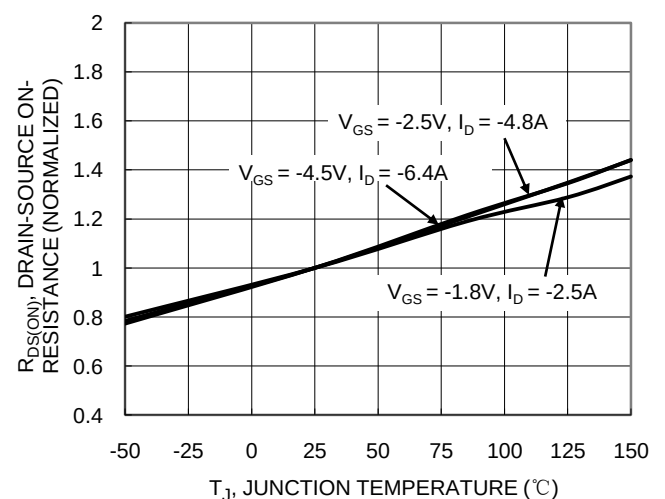


Figure 6. On-Resistance Variation with Temperature

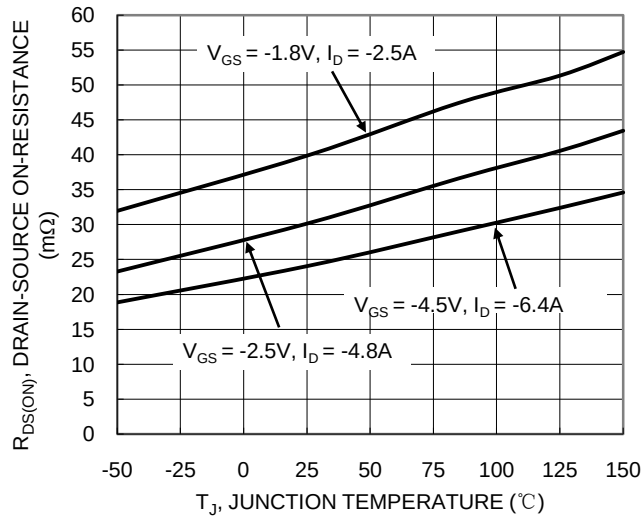


Figure 7. On-Resistance Variation with Temperature

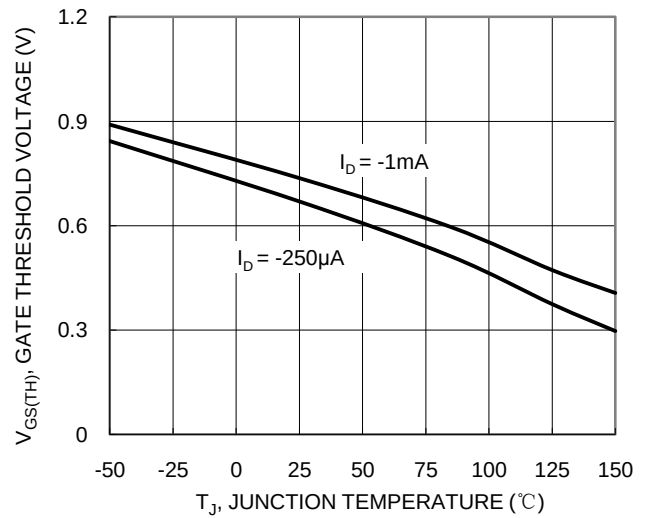


Figure 8. Gate Threshold Variation vs. Junction Temperature

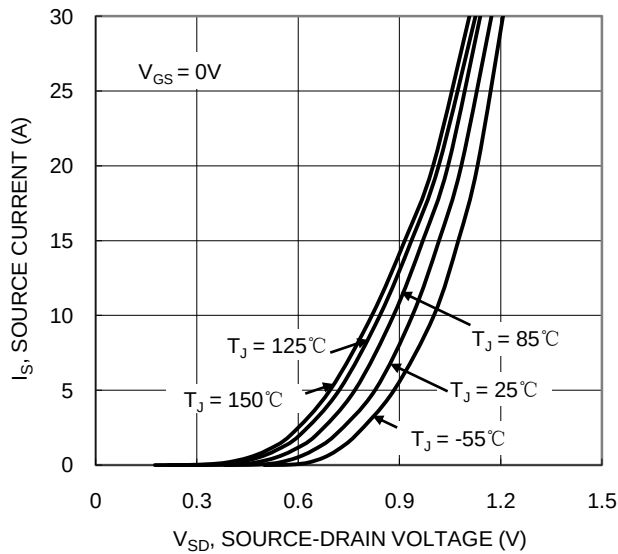


Figure 9. Diode Forward Voltage vs. Current

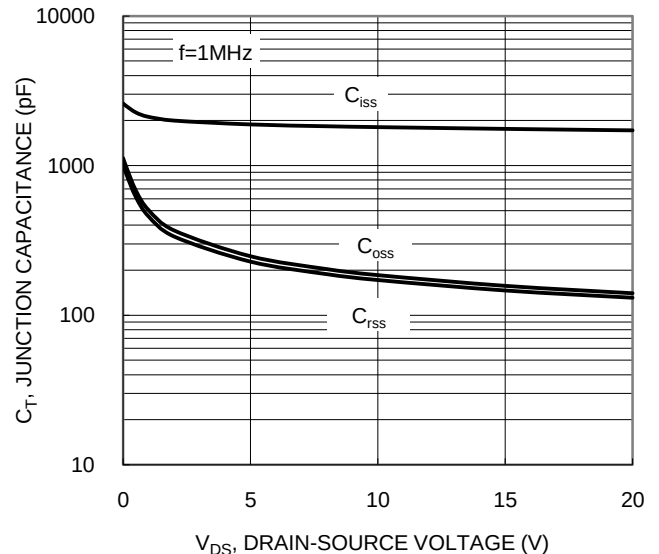


Figure 10. Typical Junction Capacitance

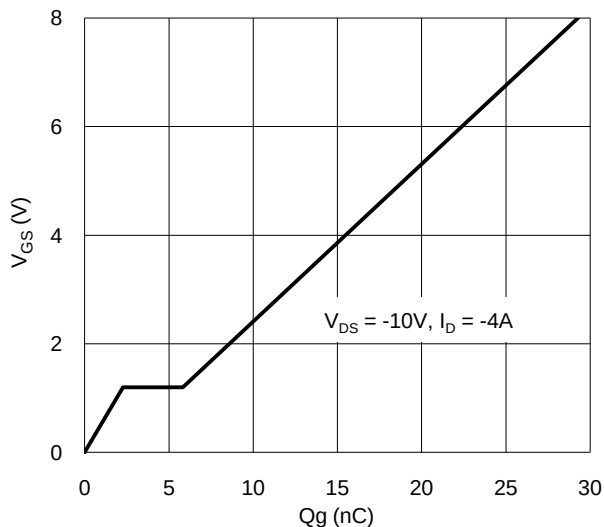


Figure 11. Gate Charge

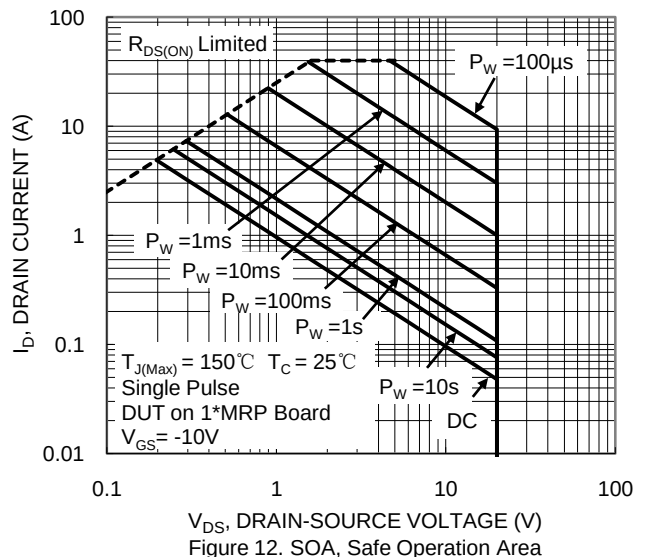


Figure 12. SOA, Safe Operation Area

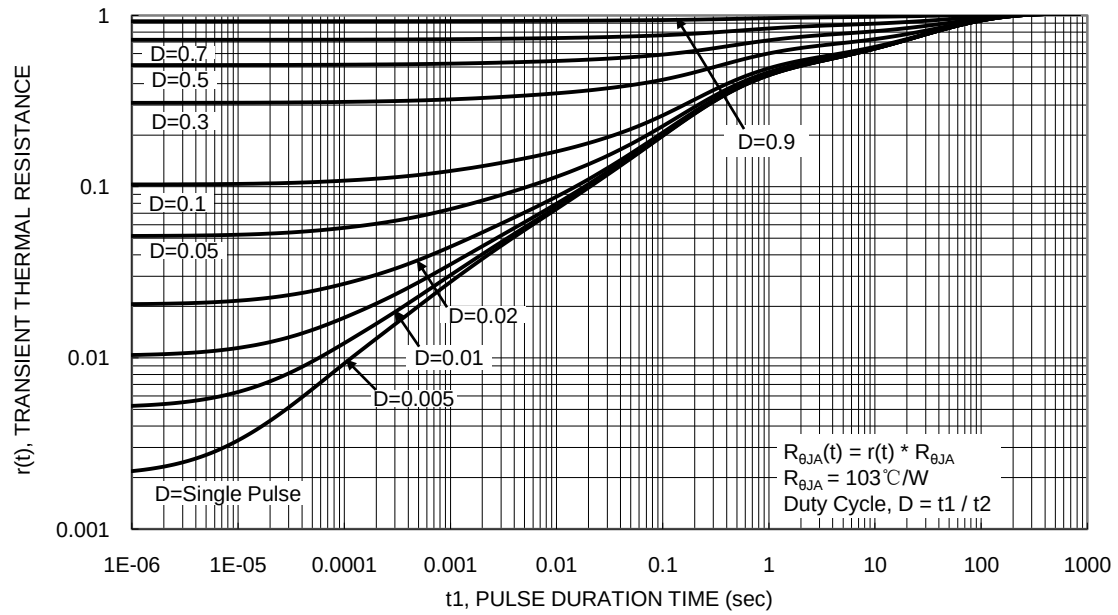
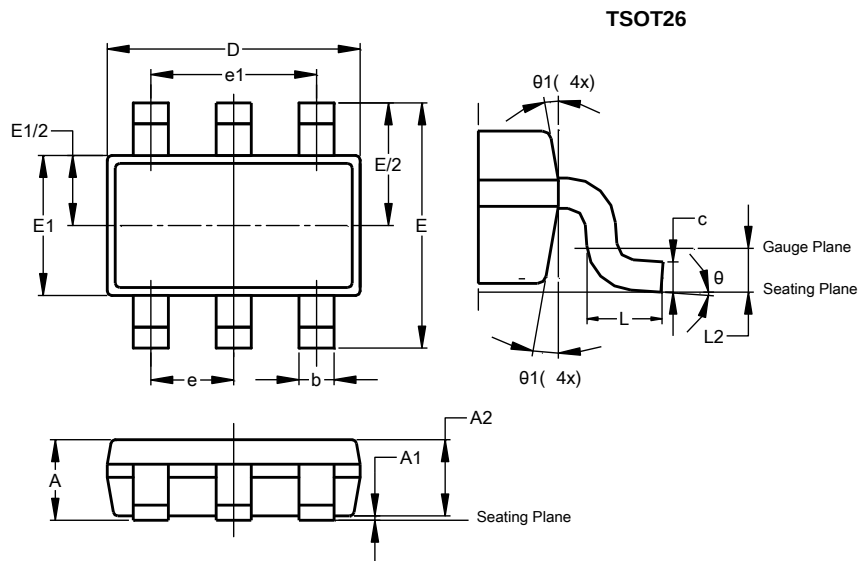


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

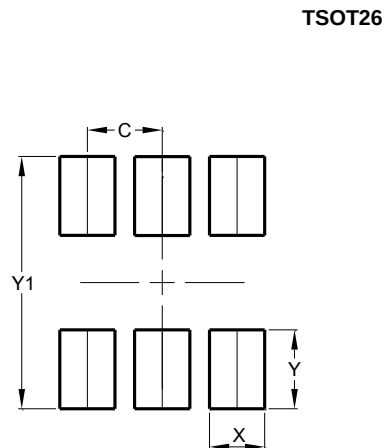
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



TSOT26			
Dim	Min	Max	Typ
A	—	1.00	—
A1	0.010	0.100	—
A2	0.840	0.900	—
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	—
c	0.120	0.200	—
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	—
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	—
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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